

Fig. 1

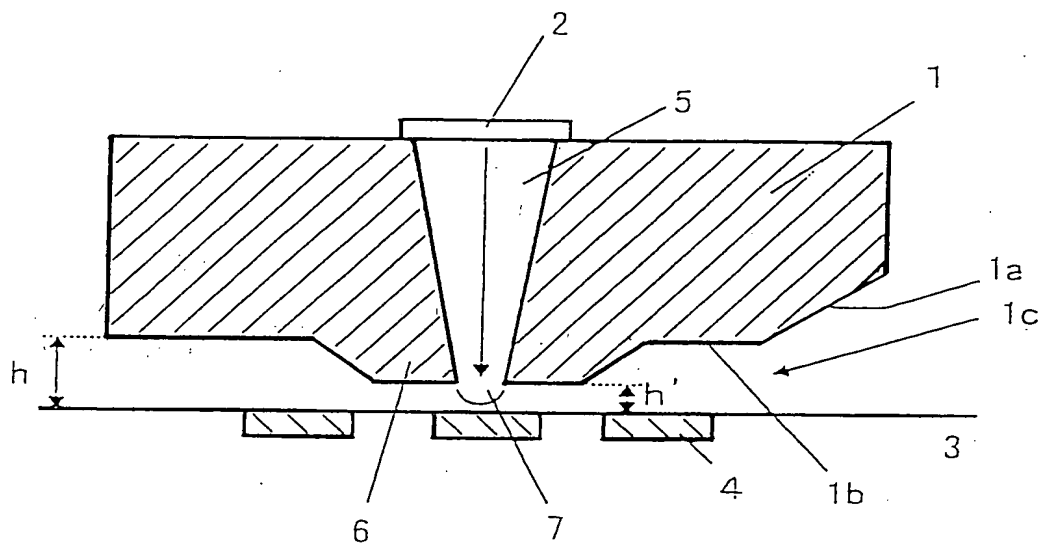
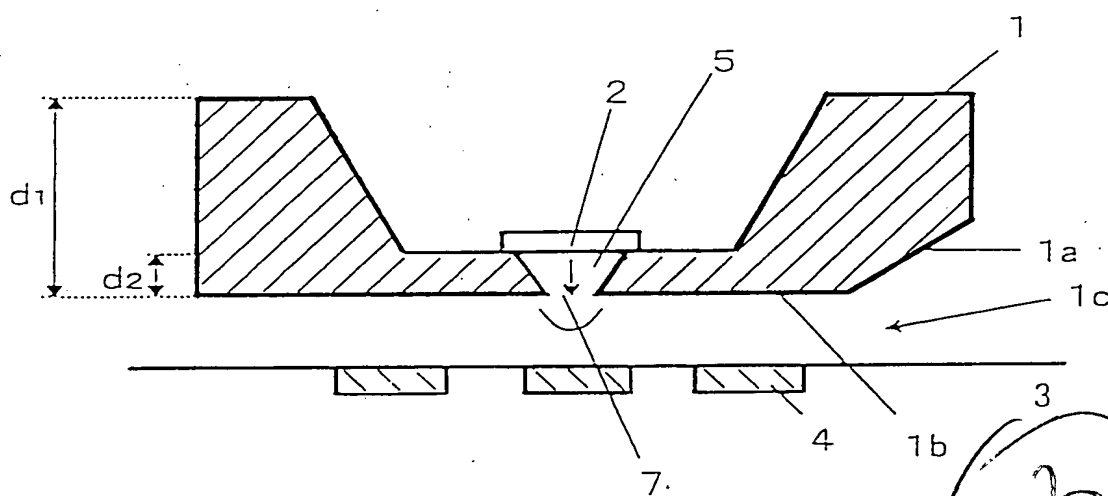


Fig. 2



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A cross-sectional view of a semiconductor device. A central gate structure (2) is positioned on a substrate (1). The substrate has a central region (1a) and side regions (1b, 1c). A central channel (7) is formed in the substrate (1a) under the gate (2). A central contact (5) is connected to the gate (2). Side contacts (8) are connected to the side regions (1b, 1c). A central contact (6) is connected to the central channel (7). The substrate (1) is supported by a base (3). The height of the substrate (1) is indicated by 'h'.

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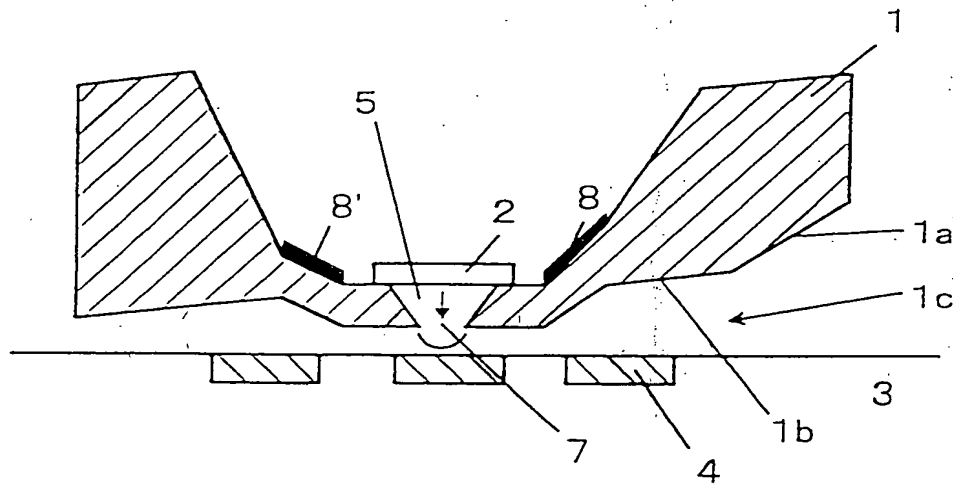


Fig. 6A

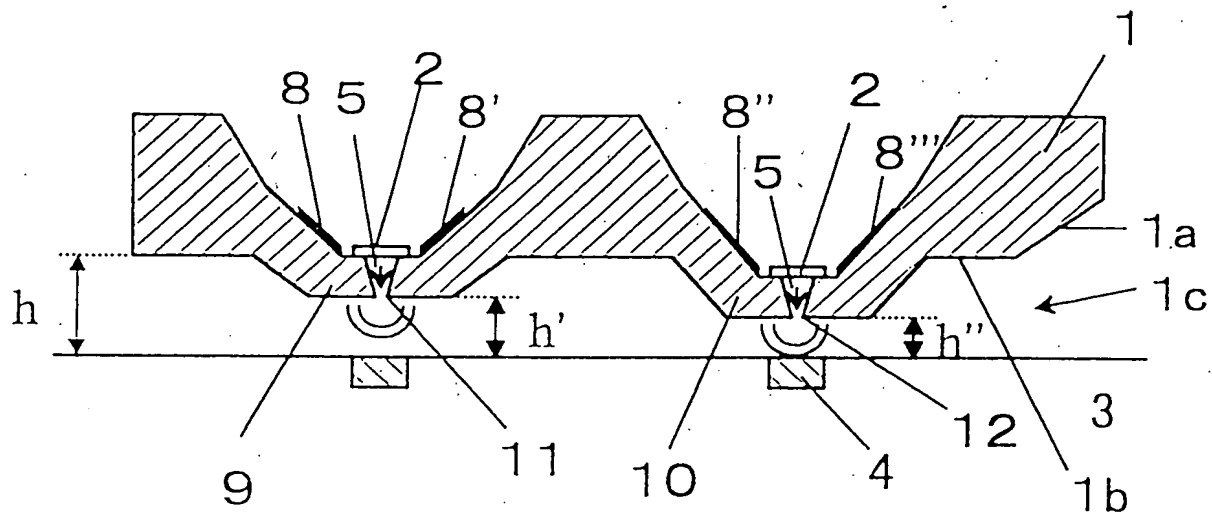


Fig. 6B

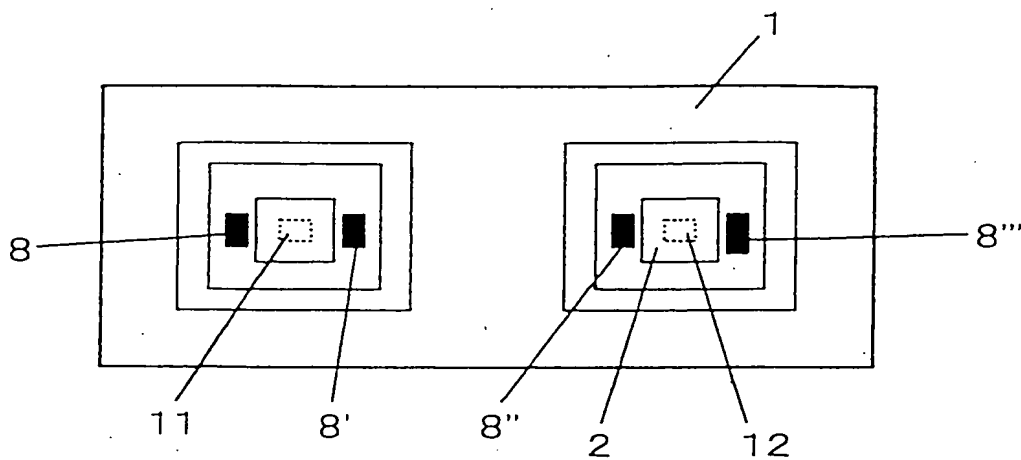


Fig. 7

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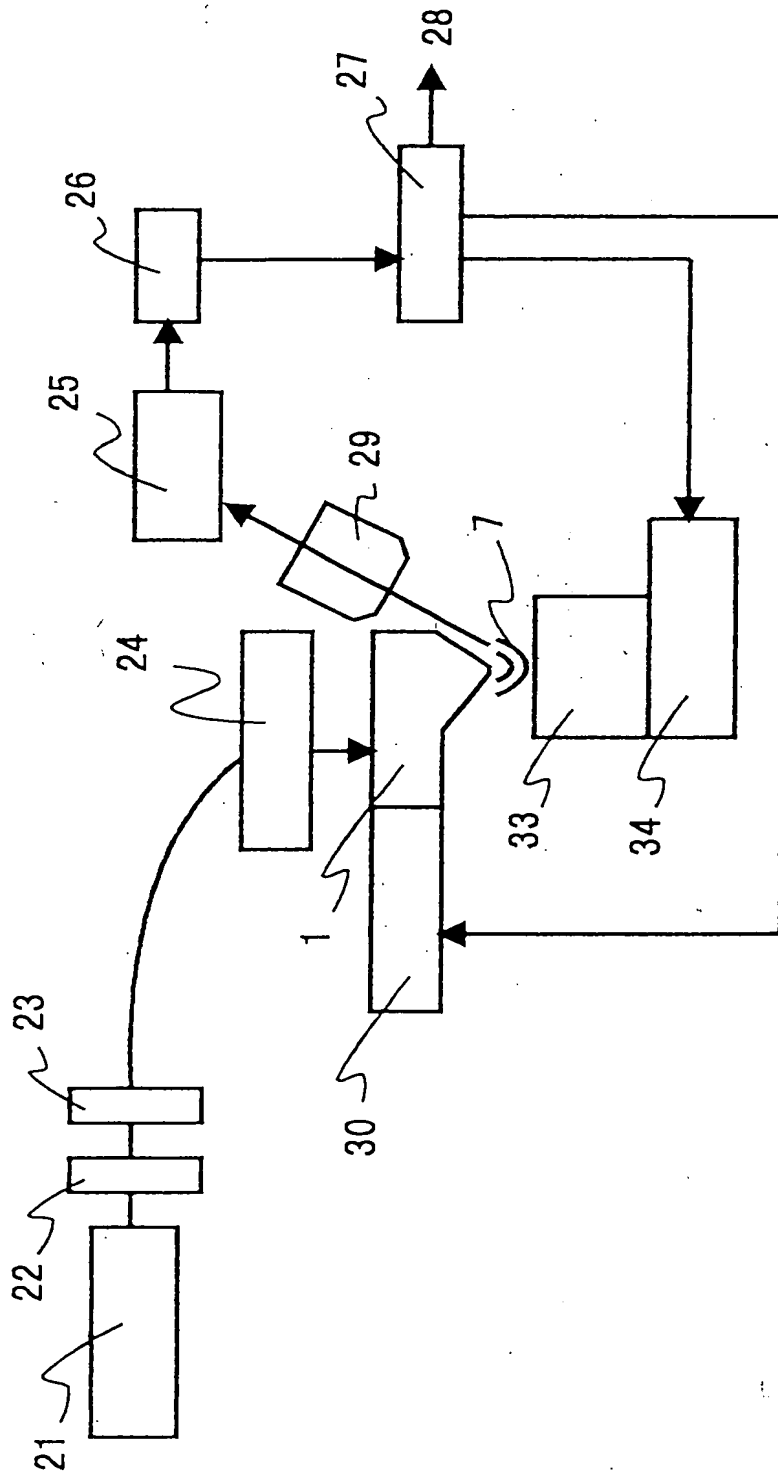


Fig. 9

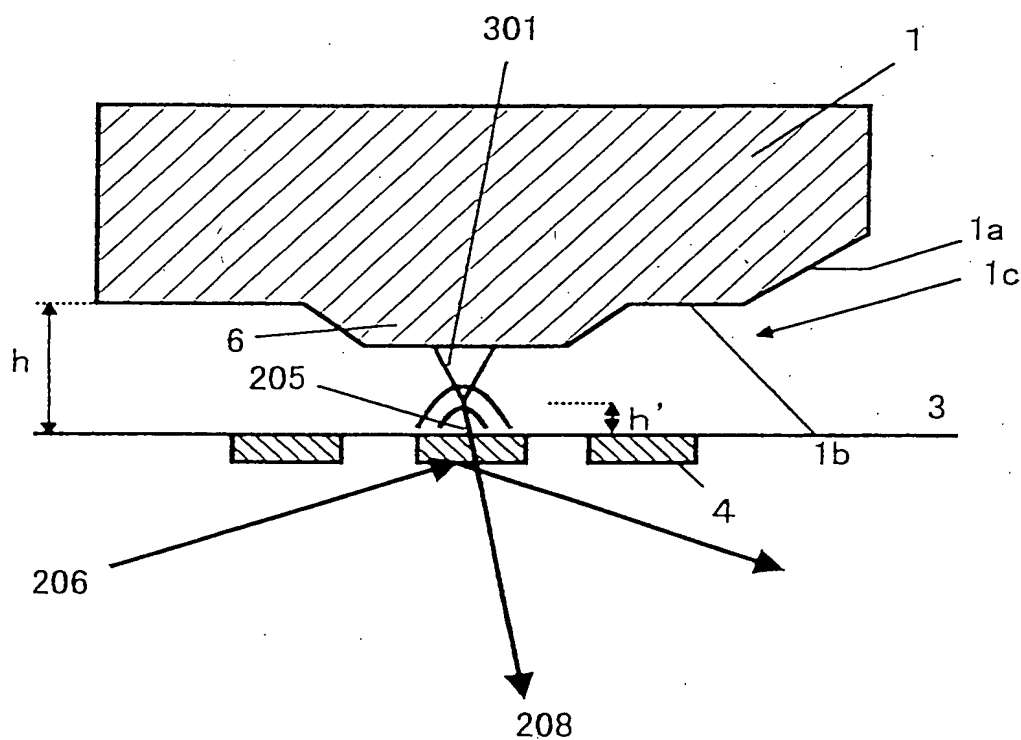
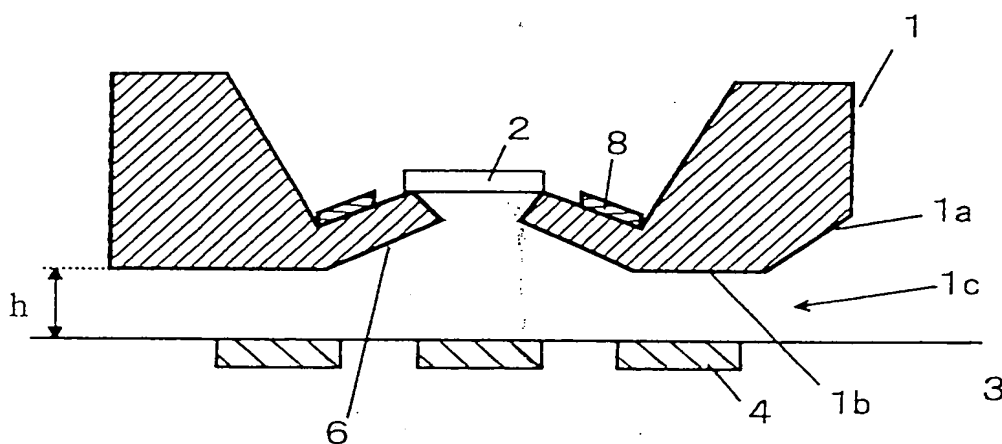


Fig. 10



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